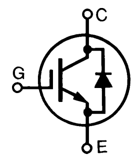
HiPerFAST™ IGBT with Diode

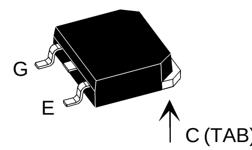
IXGH 30N60BD1
IXGT 30N60BD1

V_{CES}	=	600 V
I_{C25}	=	60 A
$V_{CE(sat)}$	=	1.8 V
$t_{fi(typ)}$	=	100 ns

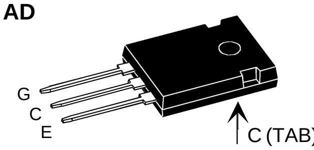


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	60	A
I_{C90}	T_C = 90°C	30	A
I_{CM}	T_C = 25°C, 1 ms	120	A
SSOA (RBSOA)	V_{GE}= 15 V, T_{VJ} = 125°C, R_G = 10 Ω Clamped inductive load, L = 100 µH	I_{CM} = 60 @ 0.8 V_{CES}	A
P_C	T_C = 25°C	200	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque, TO-247 AD	1.13/10	Nm/lb.in.
Weight	TO-247 AD	6	g
	TO-268	4	g

TO-268 (IXGT)



TO-247 AD (IXGH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard package
- Moderate frequency IGBT and antiparallel FRED in one package
- High current handling capability
- Newest generation HDMOS™ process
- MOS Gate turn-on
  - drive simplicity

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Space savings (two devices in one package)
- High power density
- Optimized $V_{ce(sat)}$ and switching speeds for medium frequency application

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
BV_{CES}	I_C = 250µA, V_{GE} = 0 V		600			V
$V_{GE(th)}$	I_C = 250 µA, V_{CE} = V_{GE}		2.5		5.0	V
I_{CES}	V_{CE} = 0.8 • V_{CES} V_{GE} = 0 V	T_J = 25°C T_J = 150°C			200 3	µA mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15 V				1.8	V

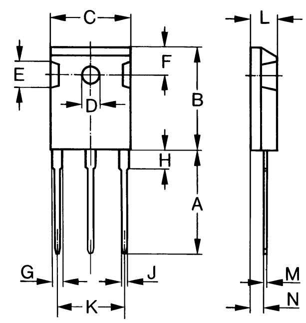
IXYS reserves the right to change limits, test conditions, and dimensions. 98510C (7/00)

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %		25		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		2700		pF
C_{oes}			240		pF
C_{res}			50		pF
Q_g	$I_C = I_{C90}$, V_{GE} = 15 V, $V_{CE} = 0.5\ V_{CES}$		110		nC
Q_{ge}			22		nC
Q_{gc}			40		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		25		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH, $V_{CE} = 0.8\ V_{CES}$, $R_G = R_{off}$ = 4.7 Ω		30		ns
$t_{d(off)}$	Remarks: Switching times may increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		130	220	ns
t_{fi}			100	190	ns
E_{off}			1.0	2.0	mJ
$t_{d(on)}$	**Inductive load, T_J = 150°C**		25		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH		35		ns
E_{on}	$V_{CE} = 0.8\ V_{CES}$, $R_G = R_{off}$ = 4.7 Ω		1.0		mJ
$t_{d(off)}$	Remarks: Switching times may increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		200		ns
t_{fi}			230		ns
E_{off}			2.5		mJ
R_{thJC}				0.62	K/W
R_{thCK}	(TO-247 AD)		0.25		K/W

Reverse Diode (FRED)

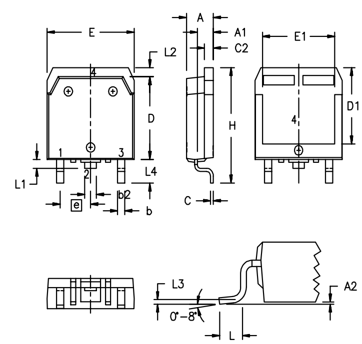
Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_F	$I_F = I_{C90}$, V_{GE} = 0 V, Pulse test T_J = 150°C			1.6	V
	t ≤ 300 µs, duty cycle d ≤ 2 %			2.5	V
I_{RM}	$I_F = I_{C90}$, V_{GE} = 0 V, $-di_F/dt$ = 100 A/µs		6		A
t_{rr}	V_R = 100 V T_J =100°C		100		ns
	I_F = 1 A; -di/dt = 100 A/µs; V_R = 30 V		25		ns
R_{thJC}				0.9	K/W

TO-247 AD (IXGH) Outline



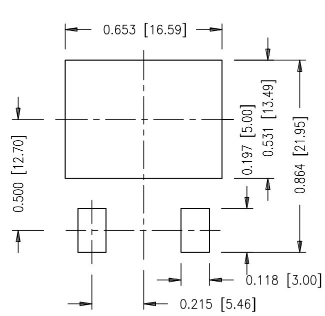
Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-268AA (D³ PAK)



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.9	5.1	.193	.201
A_1	2.7	2.9	.106	.114
A_2	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b_2	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E_1	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25 BSC		.010 BSC	
L4	3.80	4.10	.150	.161

Min. Recommended Footprint



IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:
4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

Fig. 1. Saturation Voltage Characteristics

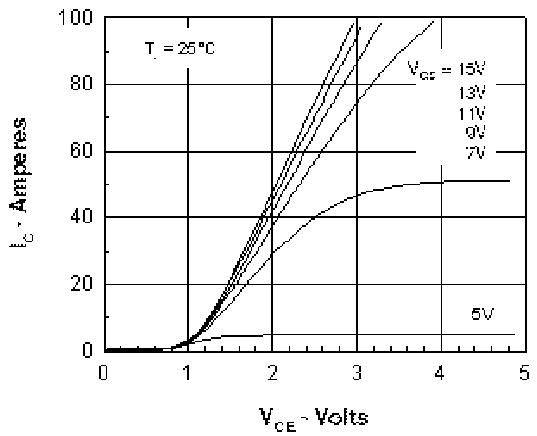


Fig. 2. Extended Output Characteristics

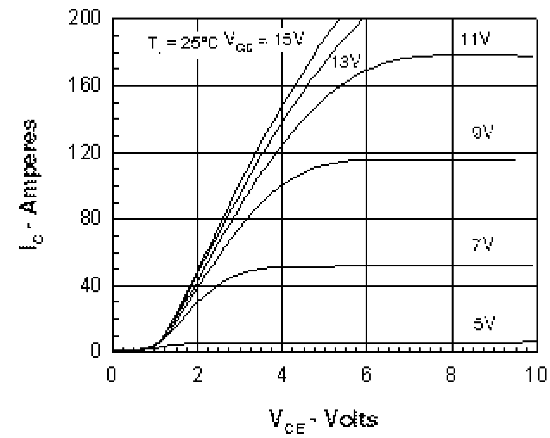


Fig. 3. Saturation Voltage Characteristics

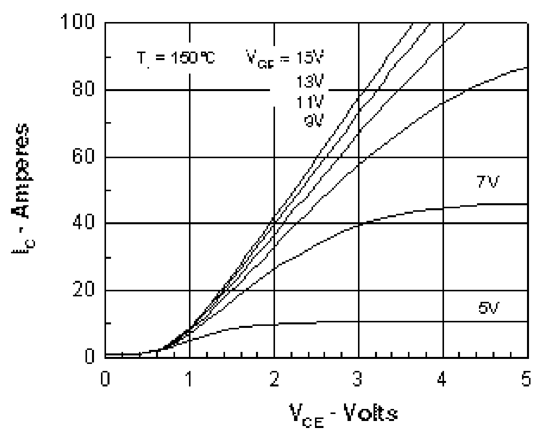


Fig. 4. Temperature Dependence of $V_{CE(sat)}$

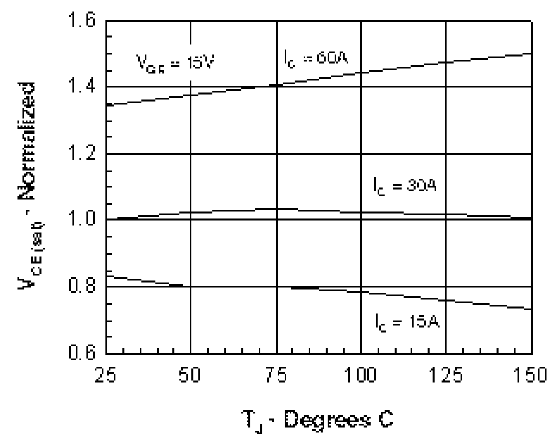


Fig. 5. Admittance Curves

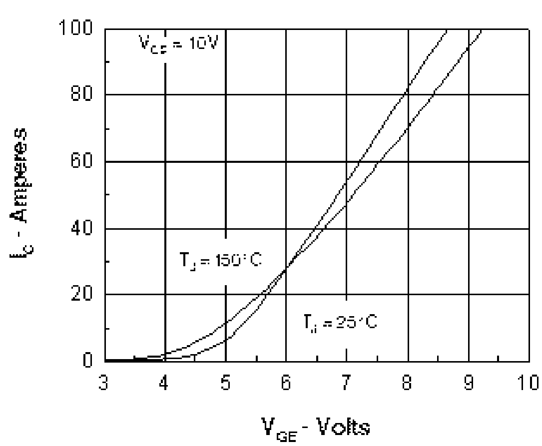


Fig. 6.Temperature Dependence of BV_{DSS} & $V_{GE(th)}$

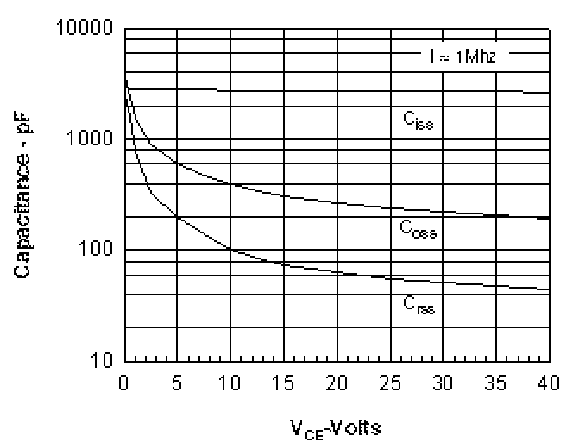


Fig. 7. Dependence of E_{OFF} and E_{OFF} on I_C.

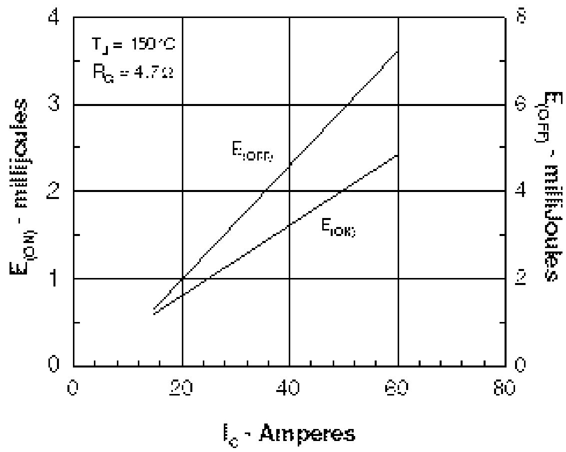


Fig. 8. Dependence of E_{OFF} on R_G.

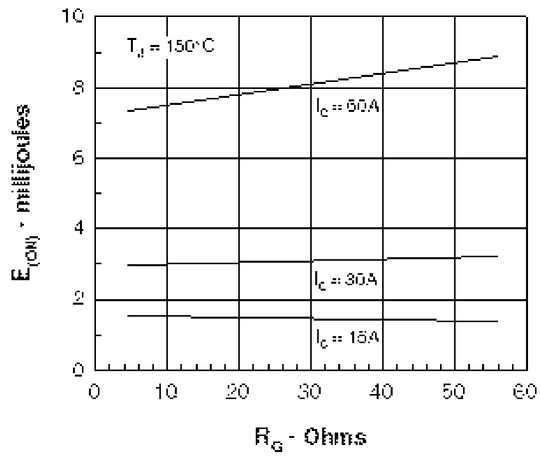


Fig. 9. Gate Charge

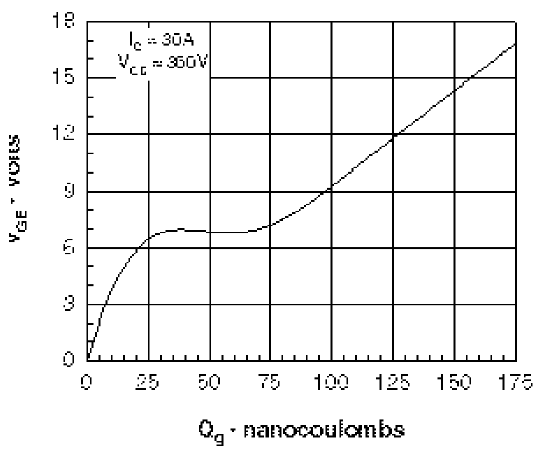


Fig. 10. Turn-off Safe Operating Area

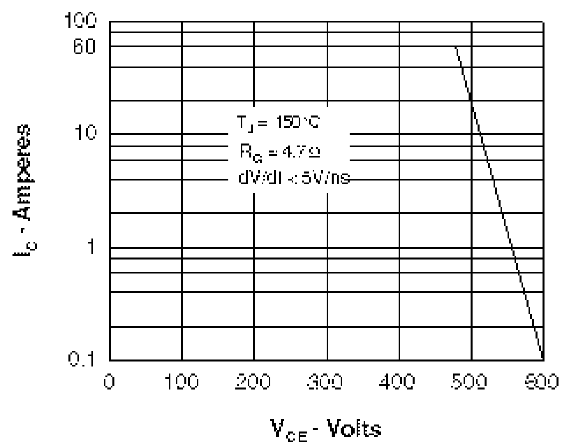
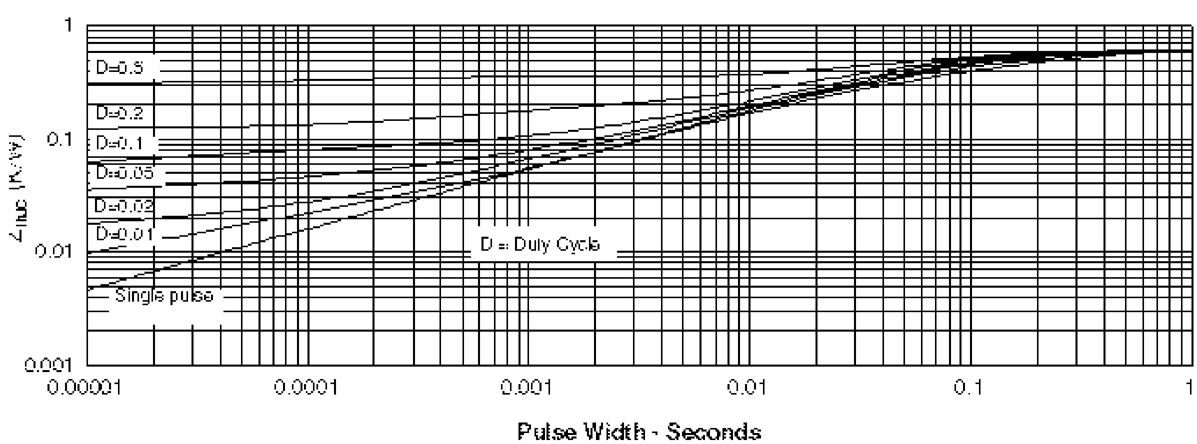


Fig. 11. IGBT Transient Thermal Resistance



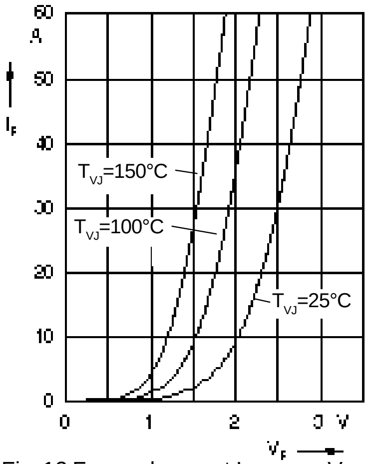


Fig. 12 Forward current I_F versus V_F

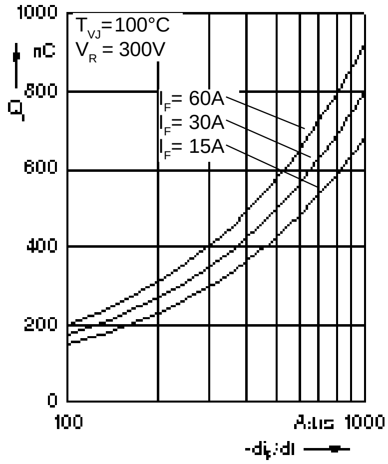


Fig. 13 Reverse recovery charge Q_r versus $-di_F/dt$

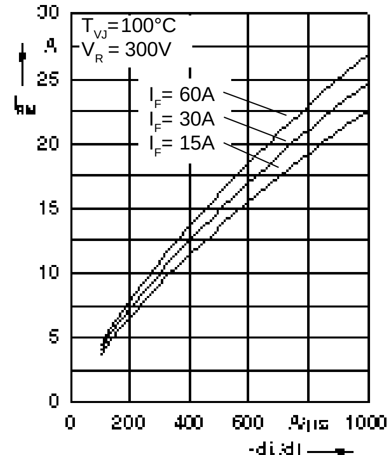


Fig. 14 Peak reverse current I_{RM} versus $-di_F/dt$

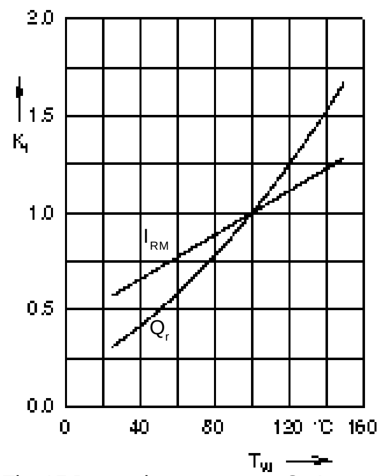


Fig. 15 Dynamic parameters Q_r, I_{RM} versus T_{VJ}

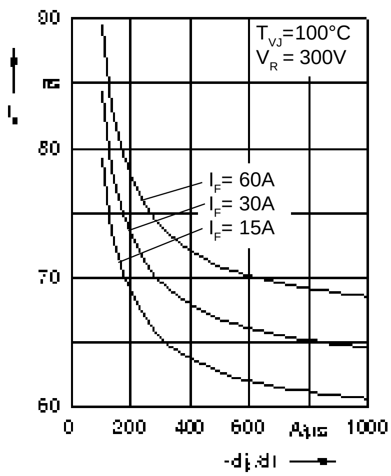


Fig. 16 Recovery time t_{rr} versus $-di_F/dt$

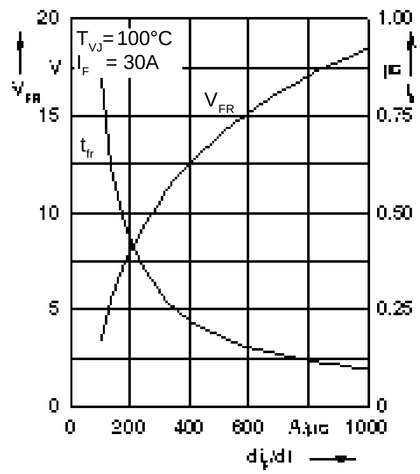


Fig. 17 Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

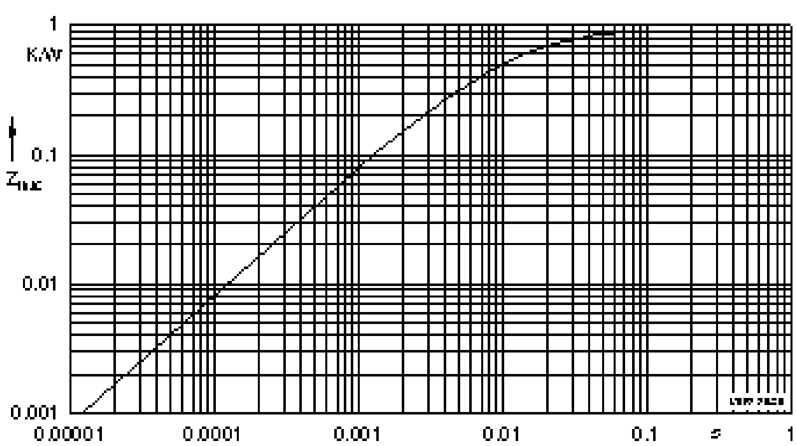


Fig. 18 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.502	0.0052
2	0.193	0.0003
3	0.205	0.0162